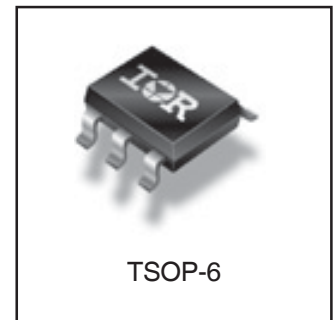
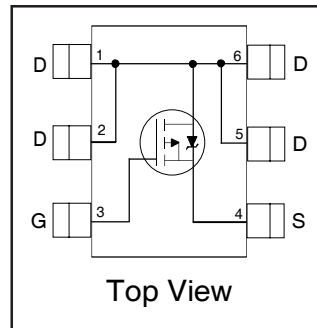


# IRFTS9342PbF

HEXFET® Power MOSFET

$V_{DS}$	<b>-30</b>	<b>V</b>
$V_{GS\ max}$	<b>±20</b>	<b>V</b>
$R_{DS(on)\ max}$ (@ $V_{GS} = -10V$ )	<b>40</b>	<b>mΩ</b>
$R_{DS(on)\ max}$ (@ $V_{GS} = -4.5V$ )	<b>66</b>	<b>mΩ</b>
$Q_g\ typ$	<b>12</b>	<b>nC</b>
$I_D$ (@ $T_A = 25^\circ C$ )	<b>-5.8</b>	<b>A</b>



## Applications

- Battery operated DC motor inverter MOSFET
- System/Load Switch

## Features and Benefits

### Features

Industry-Standard TSOP-6 Package
RoHS Compliant Containing no Lead, no Bromide and no Halogen
MSL1, Consumer Qualification

results in  
⇒

### Benefits

Multi-Vendor Compatibility
Environmentally Friendlier
Increased Reliability

Orderable part number	Package Type	Standard Pack		Note
		Form	Quantity	
IRFTS9342TRPbF	TSOP-6	Tape and Reel	3000	

## Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{DS}$	Drain-to-Source Voltage	-30	V
$V_{GS}$	Gate-to-Source Voltage	±20	
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$	-5.8	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$	-4.6	
$I_{DM}$	Pulsed Drain Current ①	-46	
$P_D @ T_A = 25^\circ C$	Power Dissipation	2.0	W
$P_D @ T_A = 70^\circ C$	Power Dissipation	1.3	
	Linear Derating Factor	0.02	W/°C
$T_J$	Operating Junction and	-55 to + 150	°C
$T_{STG}$	Storage Temperature Range		

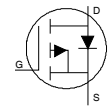
Notes ① through ④ are on page 2

## Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$BV_{DSS}$	Drain-to-Source Breakdown Voltage	-30	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	19	—	mV/°C	Reference to $25^\circ\text{C}, I_D = -1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	32	40	mΩ	$V_{GS} = -10V, I_D = -5.8A$ ③
		—	53	66		$V_{GS} = -4.5V, I_D = -4.6A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	-1.3	—	-2.4	V	$V_{DS} = V_{GS}, I_D = -25\mu A$
$\Delta V_{GS(th)}$	Gate Threshold Voltage Coefficient	—	-5.5	—	mV/°C	
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	-1.0	μA	$V_{DS} = -24V, V_{GS} = 0V$
		—	—	-150		$V_{DS} = -24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS} = -20V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS} = 20V$
$g_{fs}$	Forward Transconductance	6.8	—	—	S	$V_{DS} = -10V, I_D = -4.6A$
$Q_g$	Total Gate Charge	—	12	—	nC	$V_{DS} = -15V$
$Q_{gs}$	Gate-to-Source Charge	—	1.8	—		$V_{GS} = -10V$
$Q_{gd}$	Gate-to-Drain Charge	—	3.1	—		$I_D = -4.6A$
$R_G$	Gate Resistance	—	17	—	Ω	
$t_{d(on)}$	Turn-On Delay Time	—	4.6	—	ns	$V_{DD} = -15V, V_{GS} = -10V$ $I_D = -4.6A$ $R_G = 6.8\Omega$
$t_r$	Rise Time	—	13	—		
$t_{d(off)}$	Turn-Off Delay Time	—	45	—		
$t_f$	Fall Time	—	28	—		
$C_{iss}$	Input Capacitance	—	595	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	133	—		$V_{DS} = -25V$
$C_{riss}$	Reverse Transfer Capacitance	—	85	—		$f = 1.0\text{KHz}$

## Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	-2.0	A	MOSFET symbol showing the integral reverse p-n junction diode.
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	-46		
$V_{SD}$	Diode Forward Voltage	—	—	-1.2	V	$T_J = 25^\circ\text{C}, I_S = -4.6A, V_{GS} = 0V$ ③
$t_{rr}$	Reverse Recovery Time	—	20	30	ns	$T_J = 25^\circ\text{C}, I_F = -4.6A, V_{DD} = -24V$
$Q_{rr}$	Reverse Recovery Charge	—	11	17	nC	$di/dt = 100A/\mu s$ ③
$t_{on}$	Forward Turn-On Time	Time is dominated by parasitic inductance				

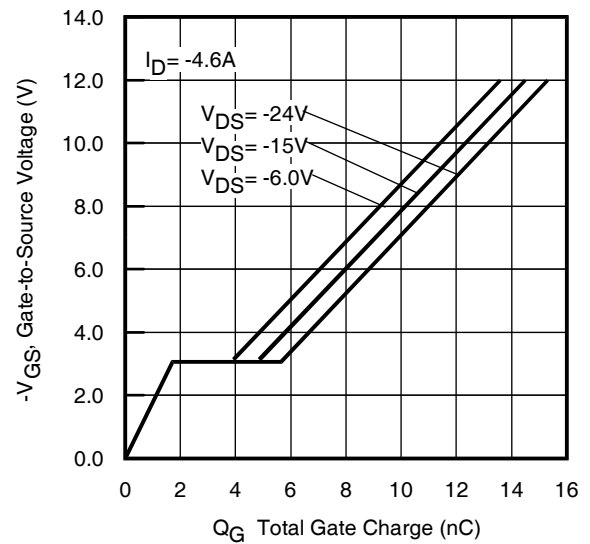
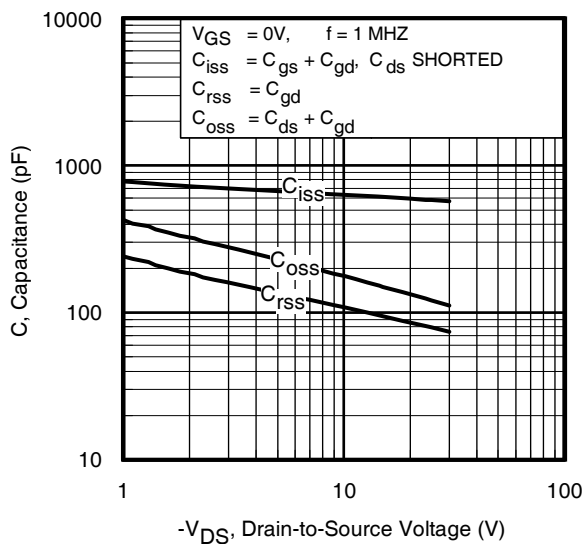
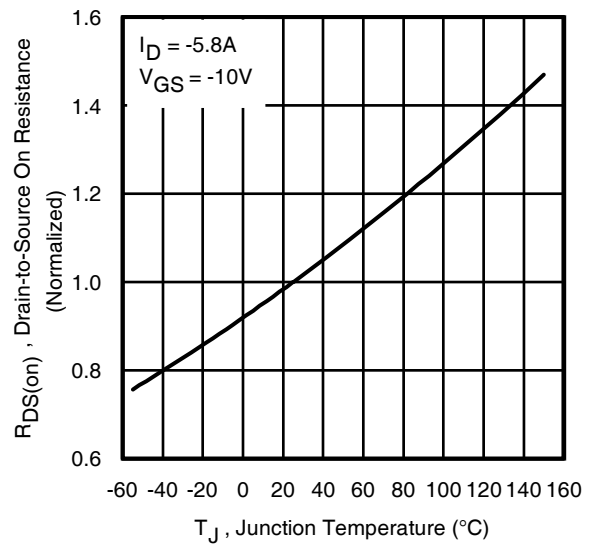
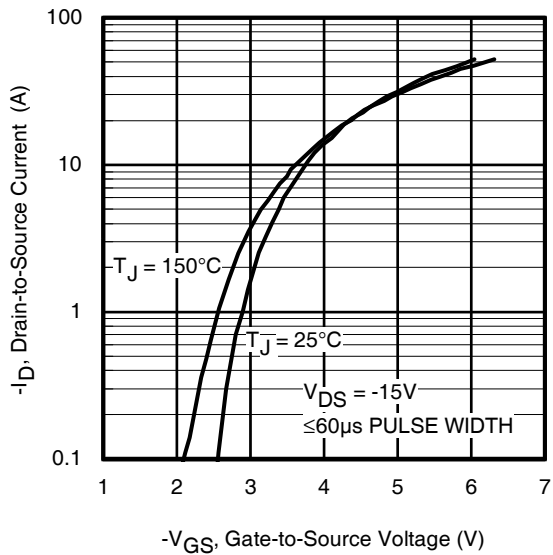
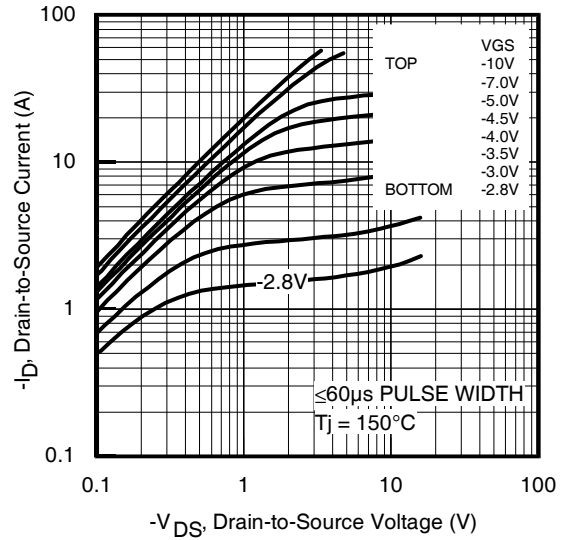
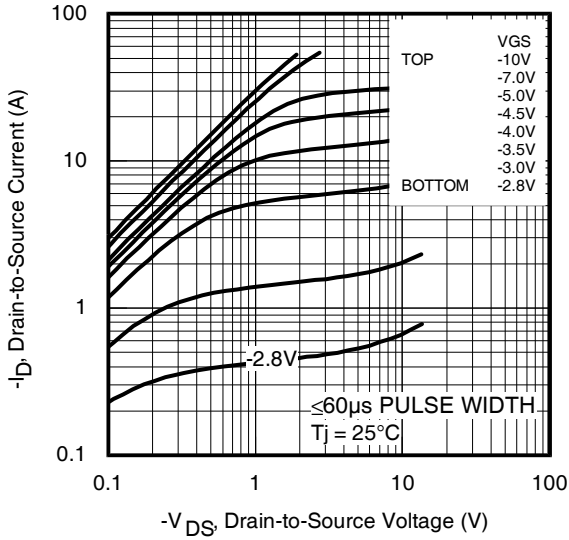


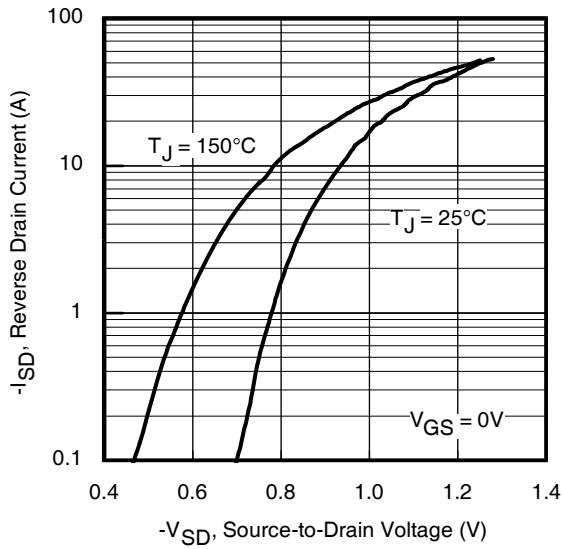
## Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient ③	—	62.5	°C/W

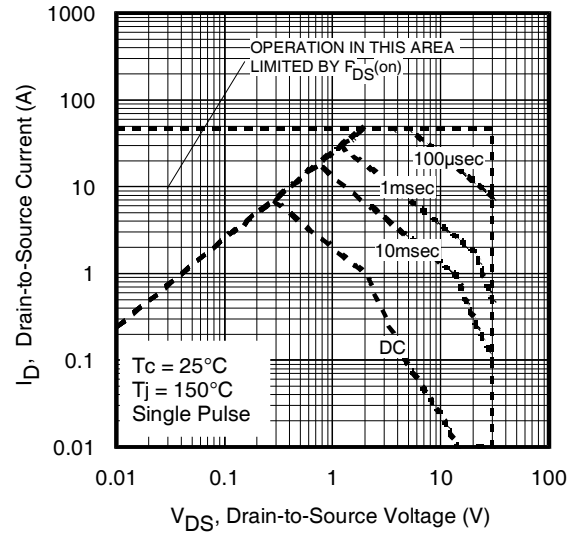
### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width  $\leq 400\mu s$ ; duty cycle  $\leq 2\%$ .
- ③ When mounted on 1 inch square copper board.

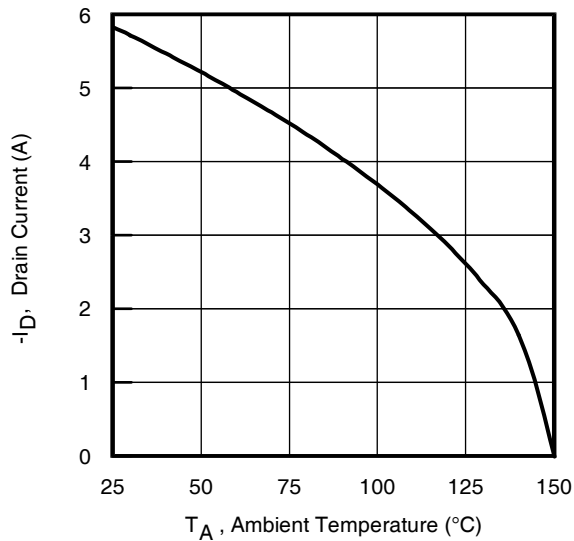




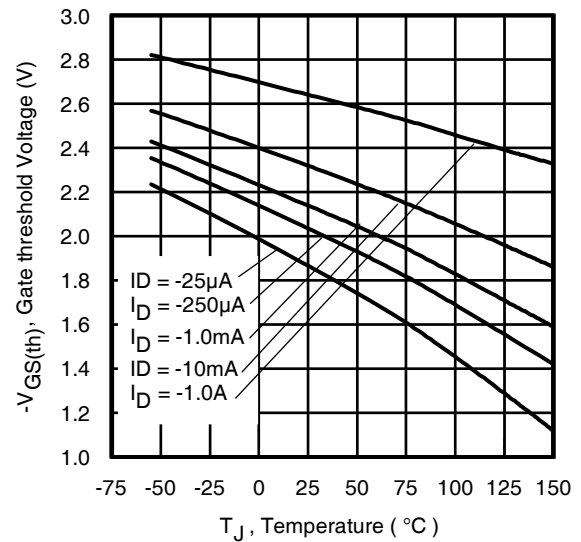
**Fig 7.** Typical Source-Drain Diode Forward Voltage



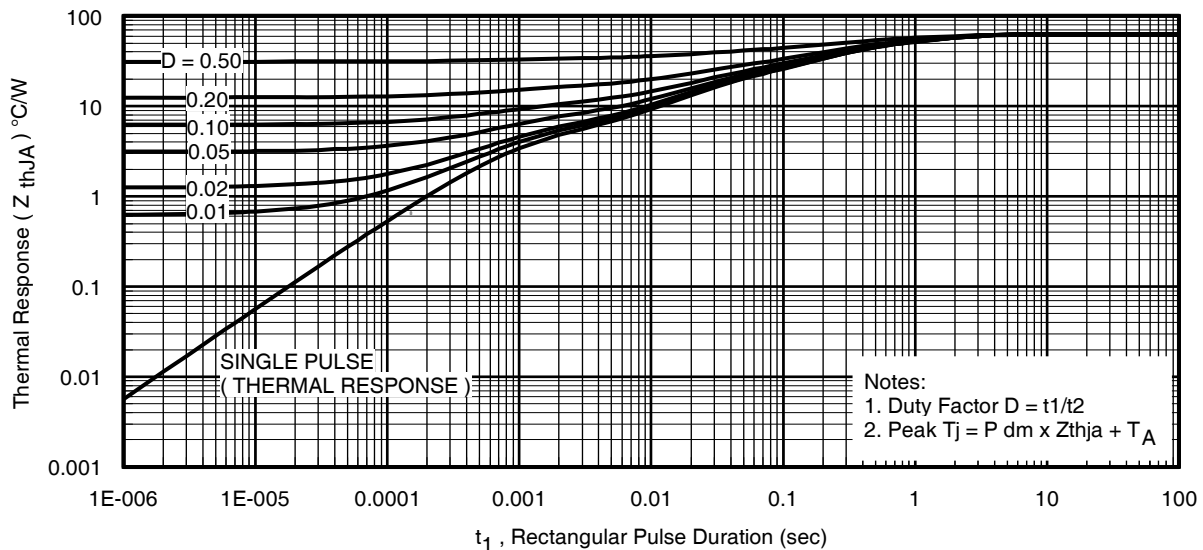
**Fig 8.** Maximum Safe Operating Area



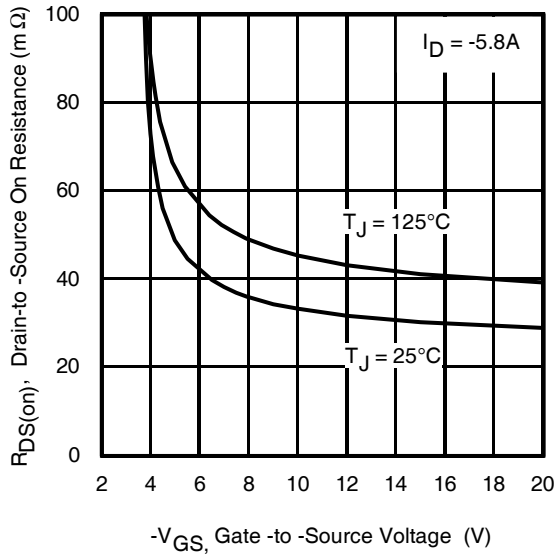
**Fig 9.** Maximum Drain Current vs. Case Temperature



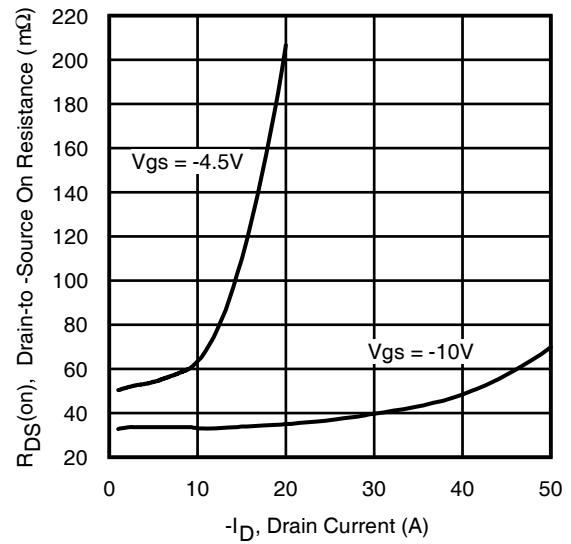
**Fig 10.** Threshold Voltage vs. Temperature



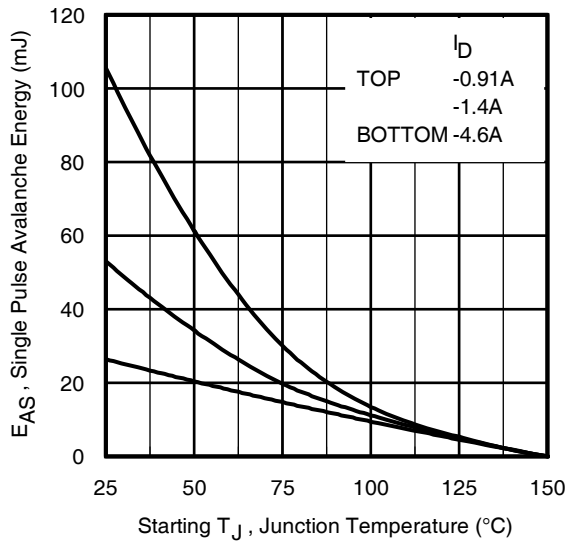
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case



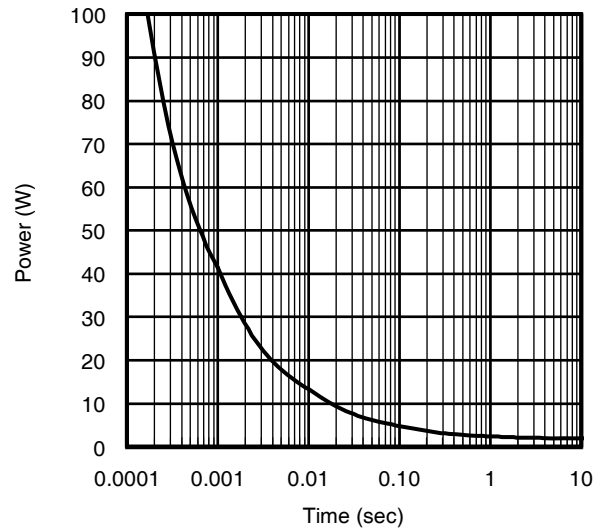
**Fig 12.** On-Resistance vs. Gate Voltage



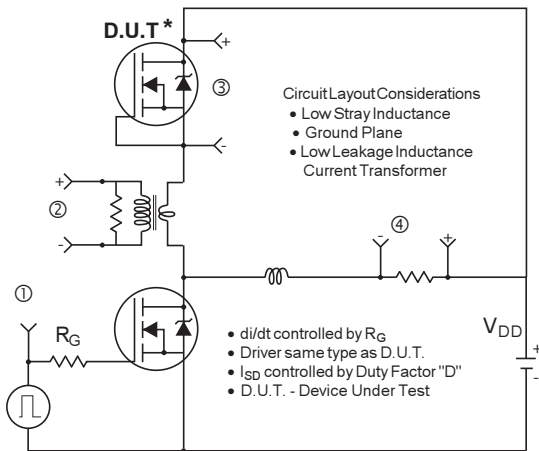
**Fig 13.** Typical On-Resistance vs. Drain Current



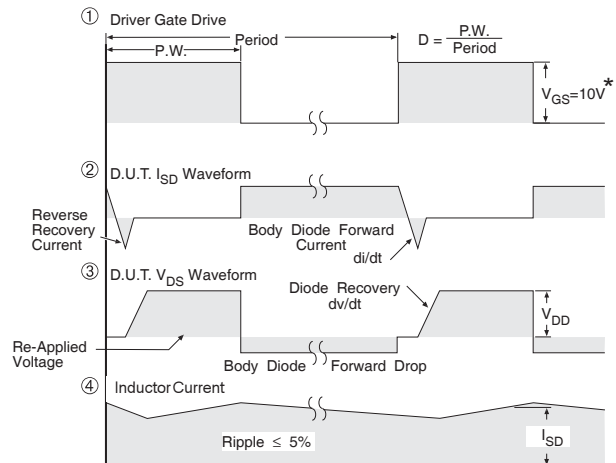
**Fig 14.** Maximum Avalanche Energy vs. Drain Current



**Fig 15.** Typical Power vs. Time

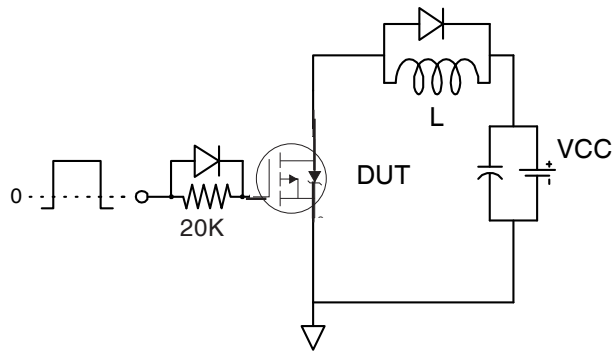


\* Reverse Polarity of D.U.T for P-Channel

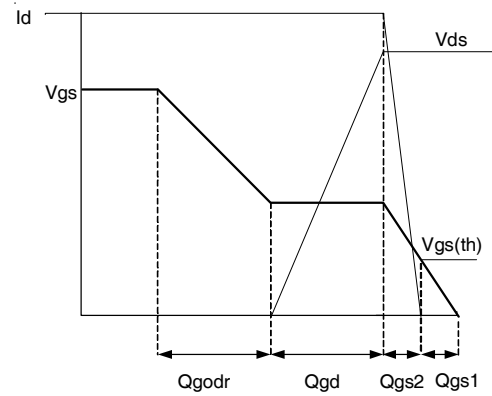


\*  $V_{GS} = 5V$  for Logic Level Devices

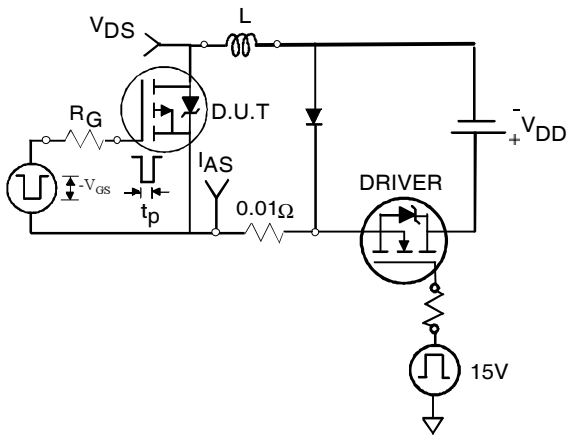
**Fig 16.** Diode Reverse Recovery Test Circuit for P-Channel HEXFET® Power MOSFETs



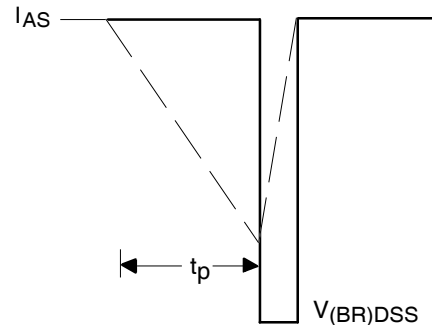
**Fig 17a.** Gate Charge Test Circuit



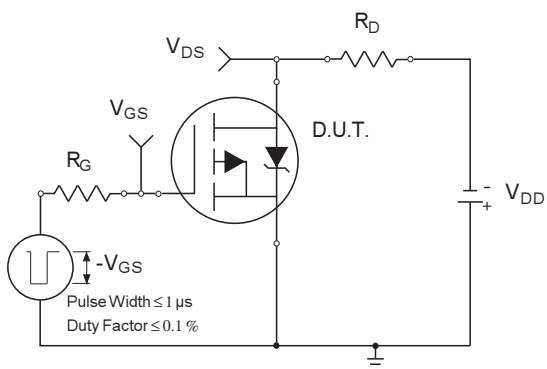
**Fig 17b.** Gate Charge Waveform



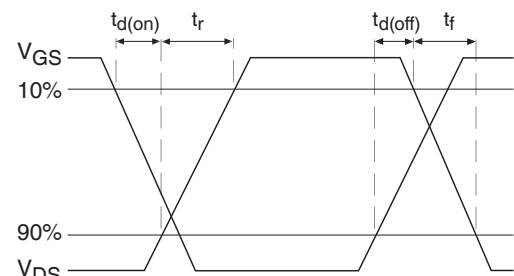
**Fig 18a.** Unclamped Inductive Test Circuit



**Fig 18b.** Unclamped Inductive Waveforms

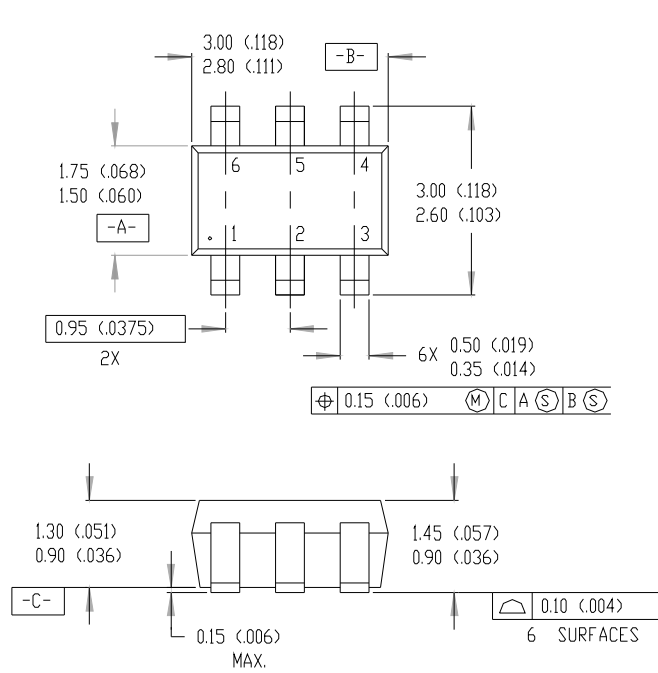


**Fig 19a.** Switching Time Test Circuit

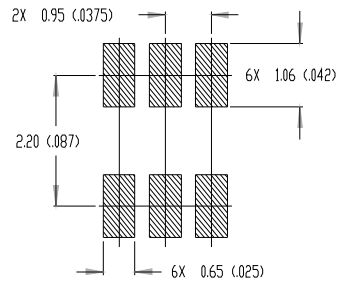


**Fig 19b.** Switching Time Waveforms

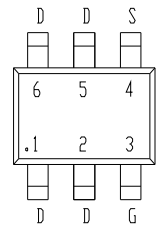
## TSOP-6 Package Outline



### MINIMUM RECOMMENDED FOOTPRINT

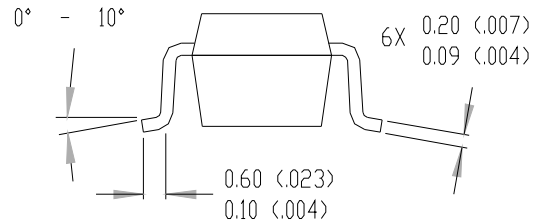


### LEAD ASSIGNMENTS

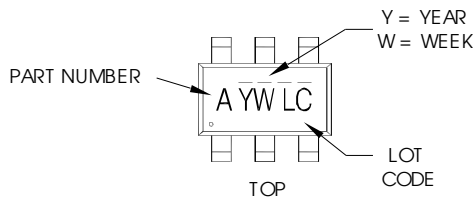


### NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).



## TSOP-6 Part Marking Information



### PART NUMBER CODE REFERENCE:

A = SI3443DV	O = IRLTS6342TRPBF
B = IRF5800	P = IRFTS8342TRPBF
C = IRF5850	R = IRFTS9342TRPBF
D = IRF5851	S = Not applicable
E = IRF5852	T = IRLTS2242TRPBF
F = IRF5801	
G = IRF5803	
H = IRF5804	
I = IRF5805	
J = IRF5806	
K = IRF5810	
N = IRF5802	

Note: A line above the work week (as shown here) indicates Lead-Free.

### DATE CODE MARKING INSTRUCTIONS

WW = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR

YEAR	Y	WORK WEEK	W
2011	2001	01	A
2012	2002	02	B
2013	2003	03	C
2014	2004	04	D
2015	2005	05	
2016	2006	06	
2017	2007	07	
2018	2008	08	
2019	2009	09	
2020	2010	24	X
		25	Y
		26	Z

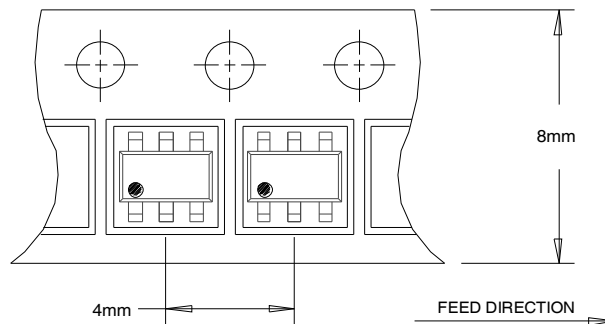
WW = (27-52) IF PRECEDED BY A LETTER

YEAR	Y	WORK WEEK	W
2011	2001	A 27	A
2012	2002	B 28	B
2013	2003	C 29	C
2014	2004	D 30	D
2015	2005	E	
2016	2006	F	
2017	2007	G	
2018	2008	H	
2019	2009	J	
2020	2010	K 50	X
		51	Y
		52	Z

Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

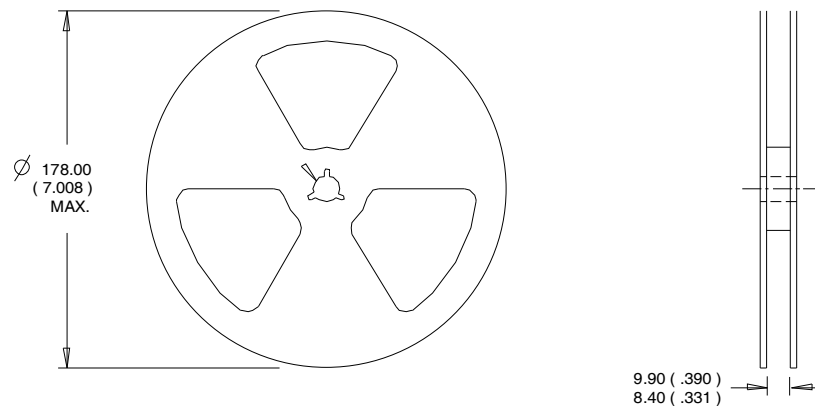
# IRFTS9342PbF

## TSOP-6 Tape and Reel Information



NOTES :

1. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES:

1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

### Qualification information<sup>†</sup>

Qualification level	Consumer <sup>††</sup> (per JEDEC JESD47F <sup>†††</sup> guidelines )	
Moisture Sensitivity Level	TSOP-6	MSL1 (per IPC/JEDEC J-STD-020D <sup>†††</sup> )
RoHS compliant	Yes	

† Qualification standards can be found at International Rectifier's web site

<http://www.irf.com/product-info/reliability>

†† Higher qualification ratings may be available should the user have such requirements.

Please contact your International Rectifier sales representative for further information:

<http://www.irf.com/whoto-call/salesrep/>

††† Applicable version of JEDEC standard at the time of product release.

Data and specifications subject to change without notice.

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